

Observation of the Ettingshausen effect in quantum Hall systems

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Evidence of the Ettingshausen effect in the breakdown regime of the integer quantum Hall effect has been observed in a GaAs/AlGaAs two-dimensional electron system. Resistance of micro Hall bars attached to both edges of a current channel shows remarkable asymmetric behaviors which indicate an electron temperature difference between the edges. The sign of the difference depends on the direction of the electric current and the polarity of the magnetic field. The results are consistent with the recent theory of Akera.

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A two-dimensional electron system (2DES) at low temperatures and in a strong magnetic field shows the quantum Hall effect (QHE), in which the longitudinal resistivity ρ_{xx} vanishes and the Hall resistance R_H in a Hall bar sample is quantized as $R_H = h/ie^2$ with an integer i .^{1,2} The quantized Hall resistance has been used as an international resistance standard since 1990.³ In order to carry out high precision measurements of the quantized Hall resistance, we must pass a large electric current through a Hall bar to generate a high Hall voltage across the sample. When the current exceeds a critical value, however, the QHE breaks down with a sharp increase in ρ_{xx} from zero.⁴ In the breakdown regime, the electron temperature T_e is expected to be much higher than the lattice temperature T_L due to the Joule heating of electrons. The hot electrons moving in the electric field carry the heat. In order to understand the mechanism of the breakdown of the QHE, it is important to know the spatial distribution of T_e and the heat flow in a Hall bar sample. In the direction of the electric current, the variation of T_e can be investigated by measuring the longitudinal resistance with a set of voltage probes distributed along the current channel.^{5,6,7,8} On the other hand, it has not been studied experimentally in the direction across the current channel.

In general, the appearance of a temperature gradient or a heat flow perpendicular to both the electric current and the magnetic field is known as the Ettingshausen effect. According to the Onsager reciprocity relations, it is the cross effect of the Nernst effect, which has been observed in 2DES's.^{9,10} Very recently, Akera has derived hydrodynamic equations for quantum Hall systems in the regime of large energy dissipation and exhibited the spatial variation of T_e in the direction perpendicular to the electric current.¹¹ His calculation shows that, although T_e is approximately uniform in the middle of the current channel, it is higher around one edge and lower around the other.

In this work, we have investigated the Ettingshausen effect in a two-dimensional GaAs/AlGaAs channel using micro Hall bars attached to both edges as indicators of T_e . Asymmetric behaviors which correspond to an electron temperature difference between the edges are observed in the QHE breakdown regime. The sign of the difference is

consistent with Akera's theory. The thermal relaxation length of hot electrons is also discussed.

The samples are fabricated on a GaAs/Al_{0.3}Ga_{0.7}As heterostructure wafer with an electron density $N_s = 2.3 \times 10^{15} \text{m}^{-2}$ and a mobility $\mu = 36 \text{m}^2/\text{Vs}$ at 4.2 K. As shown in Fig. 1(a), 600 μm wide current electrodes are separated from the central part by 1200 μm in order to avoid the effect of electron heating at the diagonally opposite corners.¹² A similar design was used by Kawaji *et al.*,¹³ who studied the intrinsic breakdown of the QHE and found the linear relationship between the critical current and the width of the central channel. The central part shown in Fig. 1(b) consists of the main channel whose width is 60 μm , four voltage probes for the measurements of I - V characteristics of the main channel, and two micro Hall bars (MHBs) attached to the main channel (see Fig. 1(c)). The longitudinal resistivity in the MHBs is expected to vary with T_e in the vicinity of each edge. All the measurements were performed at $T_L = 4.2$ K in liquid helium.

Fig. 2 shows the longitudinal voltage drop V_{MAIN} along the main channel as a function of the electric

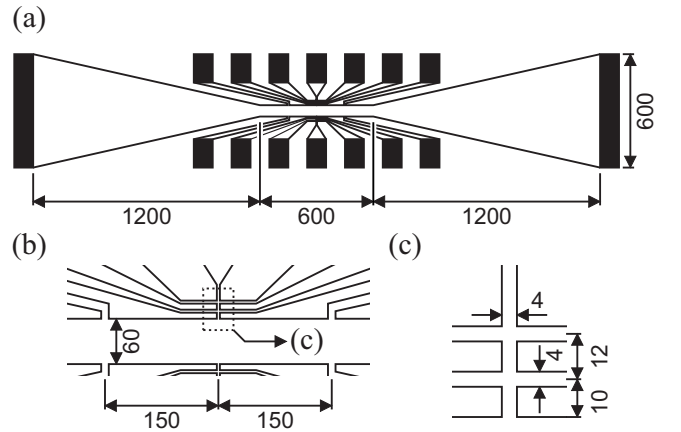


FIG. 1: Schematic view of the sample geometry. The numbers are in units of μm . (a) Overall structure. (b) Structure of the central part. (c) Micro Hall bar attached to the main channel.

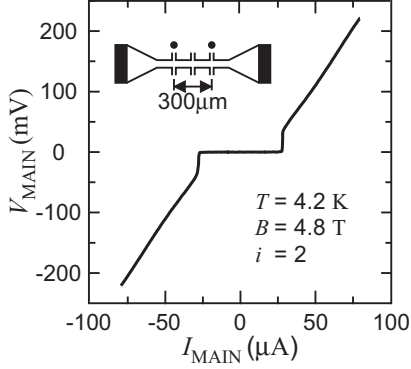


FIG. 2: I - V characteristics of the main channel.

current I_{MAIN} . The magnetic field $B = 4.8$ T corresponds to the center of the quantum Hall plateau with $i = 2$. V_{MAIN} abruptly increases at the critical current of $I_{\text{cr}} = 28.6$ μA , which is independent of the current polarity and the voltage probe pair. The critical Hall electric field $E_{\text{cr}} = 6.15$ kV/m calculated from I_{cr} is consistent with the previous measurements for the intrinsic breakdown of the QHE.^{13,14,15}

A small DC electric current I_{MHB} is used to draw a part of hot electrons from the main channel into the MHB. The differential longitudinal resistance $dV_{\text{MHB}}/dI_{\text{MHB}}$ in the MHB is measured with an AC modulation current of 0.05 μA and 26.6 Hz added to I_{MHB} . In Fig. 3, the results with $I_{\text{MHB}} = 0.2$ μA for different voltage probe pairs are shown as a function of I_{MAIN} . The critical current $I_{\text{cr}} = 28.6$ μA is indicated by arrows. The differential longitudinal resistance in the lower MHB (see Fig. 3(c) and (d)) steeply increases with I_{MAIN} for $I_{\text{MAIN}} > I_{\text{cr}}$, while the increase is small in the upper MHB in the region of $I_{\text{MAIN}} > 0$ (see Fig. 3(a) and (b)). This indicates that T_e is higher in the vicinity of the lower edge than in that of the upper edge. The electric potential due to the Hall effect is higher at the upper edge for $I_{\text{MAIN}} > 0$ and the magnetic field direction used here. The results demonstrate that T_e increases in the direction of the Hall electric field. In the case of $I_{\text{MAIN}} < 0$, the Hall electric field is reversed and a step increase in $dV_{\text{MHB}}/dI_{\text{MHB}}$ for $I_{\text{MAIN}} < -I_{\text{cr}}$ is observed in the upper MHB. The reversal of the magnetic field also changes the polarity as shown in Fig. 4(a). Similar asymmetric dependence of $dV_{\text{MHB}}/dI_{\text{MHB}}$ on I_{MAIN} at the center of the QHE plateau is observed at a lower T_L of 1.5 K, at a higher N_s of 2.6×10^{15} m^{-2} after a LED illumination, and in samples fabricated on other wafers. Fig. 4(b) shows the results at Landau level filling factors higher or lower than $\nu = 2$ at the center of the QHE plateau. Overall behaviors are similar to that at $\nu = 2$ while I_{cr} is smaller and $dV_{\text{MHB}}/dI_{\text{MHB}}$ for $|I_{\text{MAIN}}| < I_{\text{cr}}$ is larger.

The temperature difference between both edges indicates the presence of the component of the heat flow perpendicular to the electric current. Because of $\rho_{xx} > 0$ in

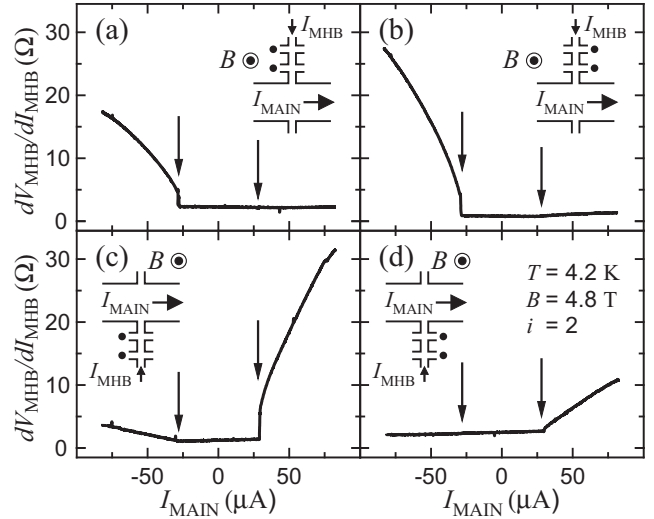


FIG. 3: Differential longitudinal resistance $dV_{\text{MHB}}/dI_{\text{MHB}}$ with $I_{\text{MHB}} = 0.2$ μA in the upper ((a) and (b)) and lower ((c) and (d)) micro Hall bars as a function of electric current I_{MAIN} through the main channel. The critical current obtained from Fig. 2 is indicated by arrows. The black dots in the insets indicate the voltage probes used in the measurements.

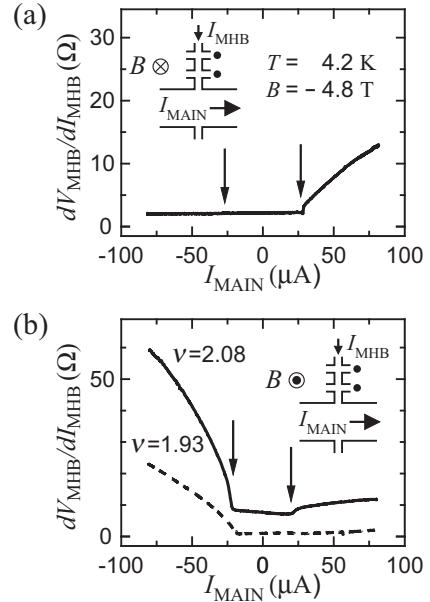


FIG. 4: Differential longitudinal resistance $dV_{\text{MHB}}/dI_{\text{MHB}}$ with $I_{\text{MHB}} = 0.2$ μA in the upper micro Hall bar. (a) Data at the reversed magnetic field. (b) Data at $\nu = 1.93$ (dashed curve) with $I_{\text{cr}} = 19.9$ μA and $\nu = 2.08$ (solid curve) with $I_{\text{cr}} = 21.0$ μA (indicated by arrows).

geometry of the other part of the sample is the same as that shown in Fig. 1. Fig. 6(b) shows the longitudinal resistivity ρ_{yy} in the MHB for different voltage probe pairs and different polarities of $I_{\text{MAIN}} \pm 50 \mu\text{A}$. The magnetic field was fixed at the center of the quantum Hall plateau with $i = 2$, where $I_{\text{cr}} = 26.9 \mu\text{A}$. T_e indicated on the right axis is estimated from T_L -dependence of the longitudinal resistivity calibrated using a sufficiently small current. The I_{MAIN} -dependence of ρ_{yy} shows that the electron temperature increases with the flux of hot electrons from the main channel. The dependence of ρ_{yy} on the distance from the main channel is negative and associated with the thermal relaxation of hot electrons during transport. In the case of $I_{\text{MAIN}} = 0$ or $I_{\text{MHB}} < 0$ (not shown in the figure), such dependence on the distance is not observed and the increase in ρ_{yy} is very small except in the region of $|I_{\text{MHB}}| \gtrsim 1.5 \mu\text{A}$ where the intrinsic (local) breakdown occurs in the MHB. Since I_{MAIN} is not directly related to the thermal relaxation process in the MHB, the dependence of ρ_{yy} on the polarity of I_{MAIN} should be attributed to the difference in T_e in the vicinity of the upper edge of the main channel due to the Ettingshausen effect discussed above.

Although the origin of the breakdown of the QHE is not clear at the present stage,⁴ the calculation of the critical electric field E_{cr} based on the heat instability model gives an upper limit of the relaxation time τ_e of hot electrons. Using $E_{\text{cr}} = (2\hbar/m^*\tau_e)^{1/2}B$ derived in Ref. 18, $\tau_e = 2.2 \text{ ns}$ is obtained from the experimental value of

$E_{\text{cr}} = 5.79 \text{ kV / m}$. Here, m^* is the effective mass of electrons in GaAs (0.067 of the free electron mass). If every hot electron in the MHB propagates with a mean velocity v_{MHB} , the relaxation length is estimated to be only $1.4 \mu\text{m}$ or less for $I_{\text{MHB}} = 1 \mu\text{A}$ ($v_{\text{MHB}} = 695 \text{ m/s}$). This seems consistent with the fact that, even for the closest voltage probe pair (a-b) with a distance of $10 \mu\text{m}$ from the main channel, ρ_{yy} is much smaller than the longitudinal resistivity ($\rho_{xx} = 610 \Omega$) in the main channel. The thermal relaxation length ℓ_{edge} that determines the spatial variation of T_e in the vicinity of the edges of the main channel can also be estimated from τ_e . For example, the y -component of the drift velocity along the equipotential lines is calculated to be 109 m/s for $|I_{\text{MAIN}}| = 50 \mu\text{A}$. It leads to a very small value of $\ell_{\text{edge}} = 0.24 \mu\text{m}$. The change in T_e due to the y -component of the heat flow is expected to be confined to narrow areas in the vicinity of the edges, while a random potentials or electron-electron interactions might change ℓ_{edge} .

In summary, we have observed evidence of the Ettingshausen effect in the breakdown regime of the integer quantum Hall effect. The electron temperature difference between the edges of a long current channel is explained by a heat flow along the equipotential lines.

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